

## WNM3053

### Single N-Channel, 30V, 14.5A, Power MOSFET

[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

V <sub>DS</sub> (V)	Typical R <sub>DS(on)</sub> (mΩ)
30	6.5 @ V <sub>GS</sub> = 10V
	9.0 @ V <sub>GS</sub> = 4.5V



### Descriptions

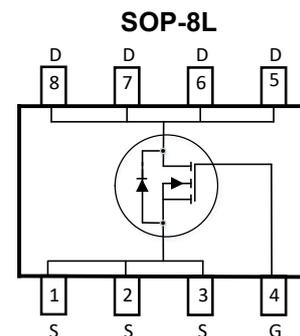
The WNM3053 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNM3053 is Pb-free.

### Features

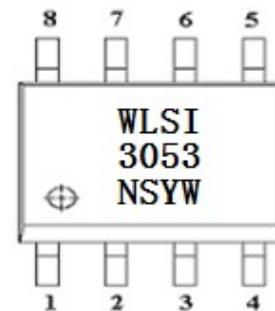
- Trench Technology
- Supper high density cell design
- Excellent ON resistance
- Extremely Low Threshold Voltage
- Small package SOP-8L

### Applications

- DC/DC converters
- Power supply converters circuit
- Load/Power Switching for portable device



Pin configuration (Top view)



3053 = Device Code  
 NS = Special Code  
 Y = Year  
 W = Week(A~z)

### Marking

### Order information

Device	Package	Shipping
WNM3053-3/TR	SOP-8L	4000/Tape&Reel

**Absolute Maximum ratings**

Parameter	Symbol	Maximum	Unit	
Drain-Source Voltage	$V_{DS}$	30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	14.5	A
		$T_A=70^\circ\text{C}$	11.5	
Pulsed Drain Current <sup>c</sup>	$I_{DM}$	60		
Maximum Power Dissipation <sup>b</sup>	$P_D$	$T_A=25^\circ\text{C}$	3.1	W
		$T_A=70^\circ\text{C}$	2.0	
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ\text{C}$	
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ\text{C}$	

**Thermal resistance ratings**

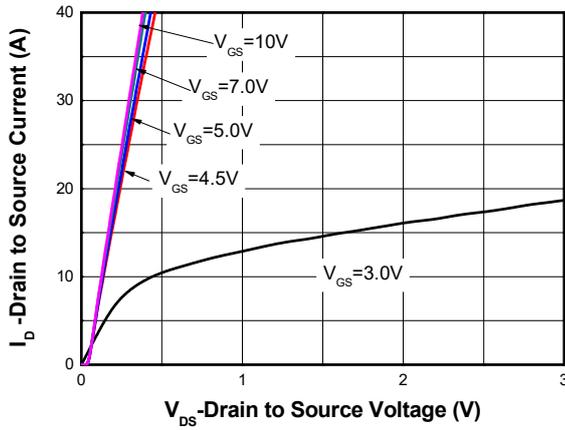
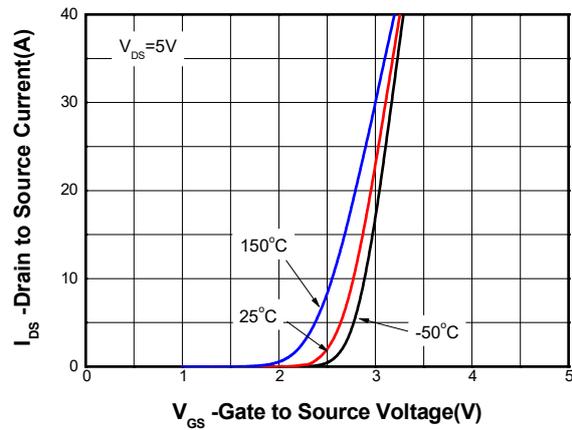
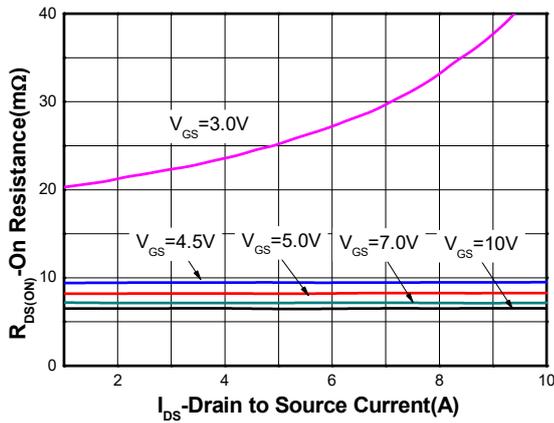
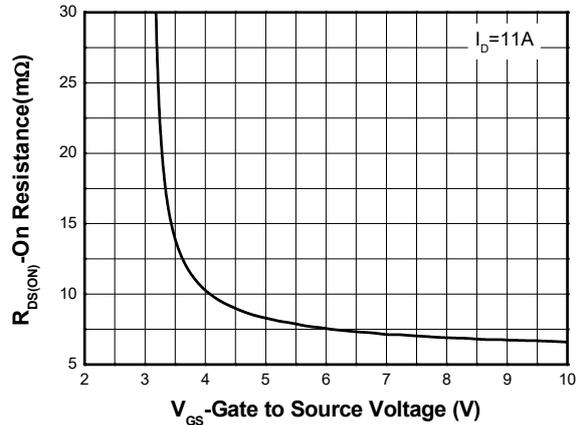
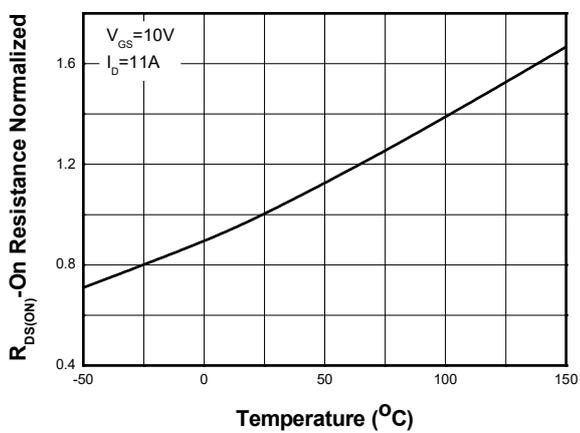
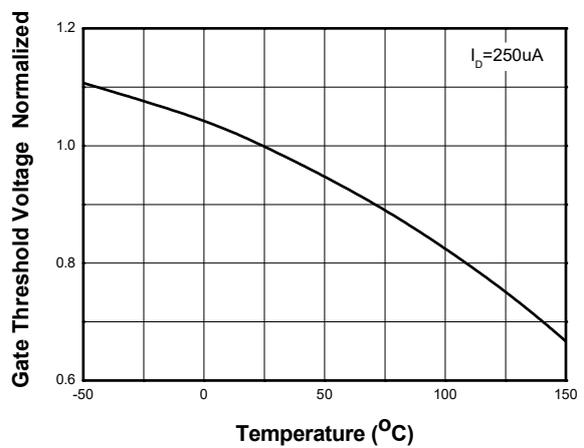
Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance <sup>a</sup>	$t \leq 10\text{ s}$	$R_{\theta JA}$	32	42	$^\circ\text{C/W}$
	Steady State		63	78	
Junction-to-Lead Thermal Resistance	Steady State	$R_{\theta JL}$	18	23	

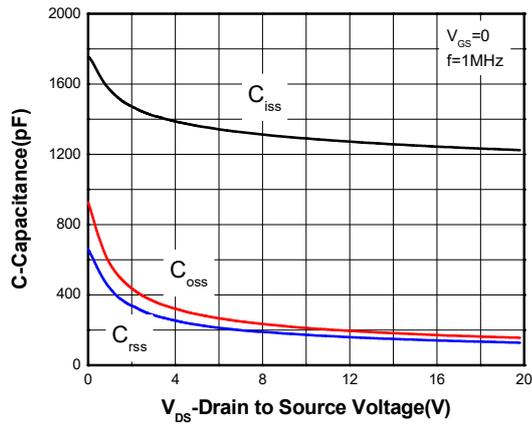
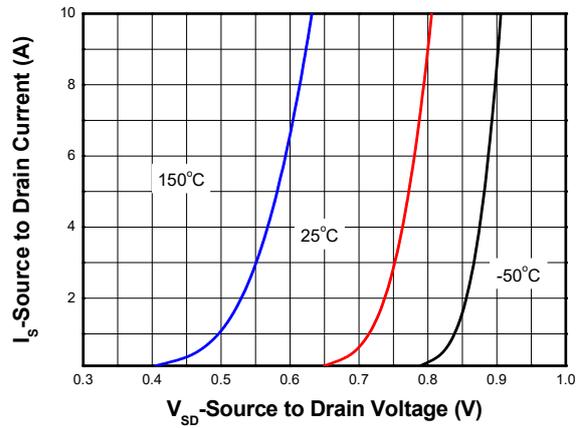
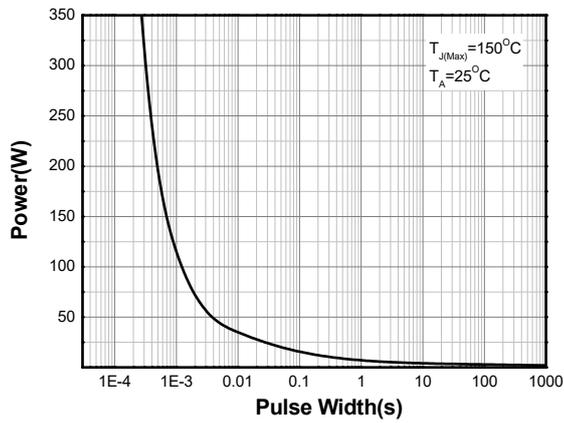
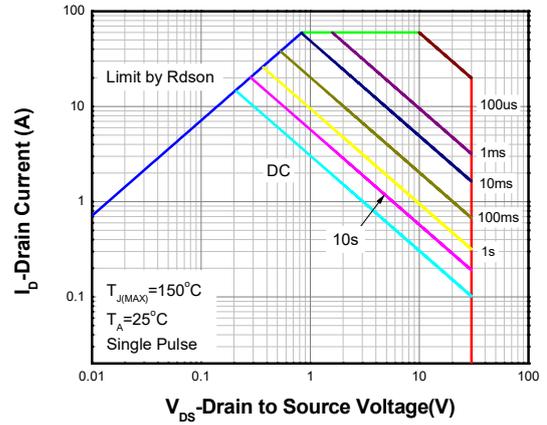
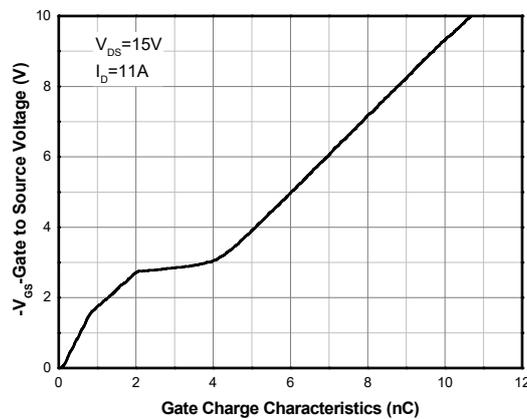
**Note:**

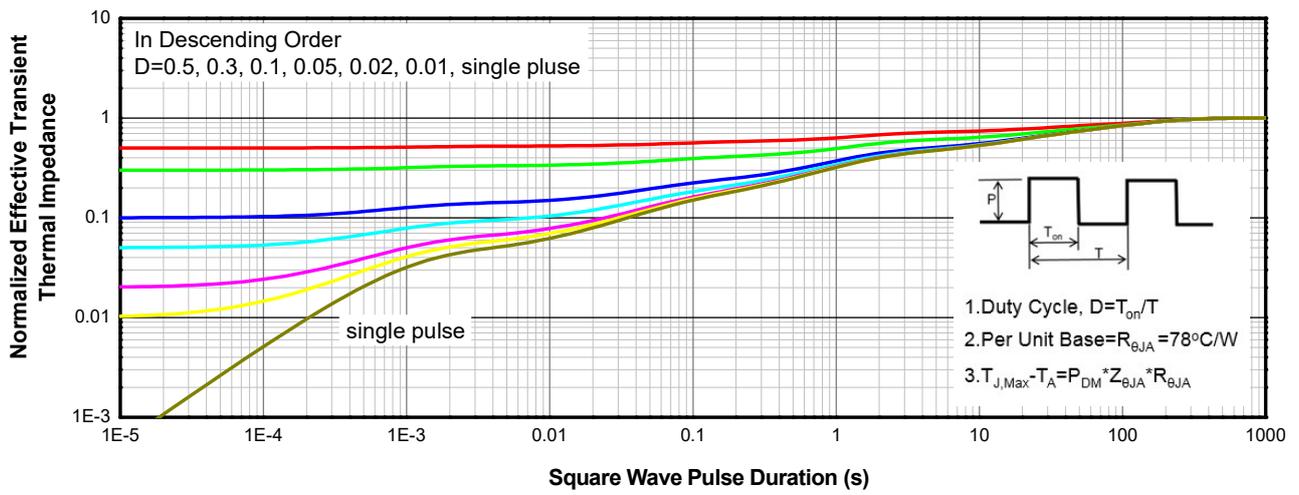
- The value of  $R_{\theta JA}$  is measured with the device mounted on 1-inch<sup>2</sup> (6.45cm<sup>2</sup>) with 2oz.(0.071mm thick) Copper pad on a 1.5\*1.5 inch<sup>2</sup>, 0.06-inch thick FR4 PCB, in a still air environment with  $T_A = 25^\circ\text{C}$ . The value in any given application is determined by the user's specific board design
- The power dissipation  $P_D$  is based on Junction-to-Ambient thermal resistance  $R_{\theta JA}$   $t \leq 10\text{s}$  value and the  $T_{J(\text{MAX})}=150^\circ\text{C}$ .
- Repetitive rating, ~10us pulse width, duty cycle ~1%, keep initial  $T_J = 25^\circ\text{C}$ , the maximum allowed junction temperature of 150 $^\circ\text{C}$ .
- The static characteristics are obtained using ~380us pulses, duty cycle ~1%.

**Electronics Characteristics (Ta=25°C, unless otherwise noted)**

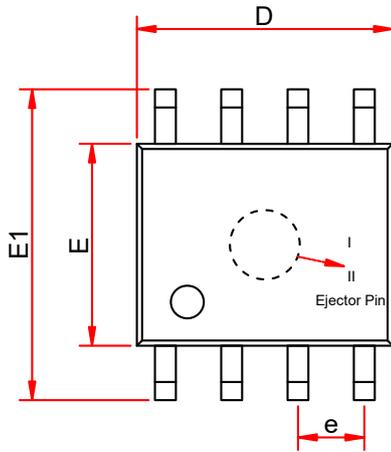
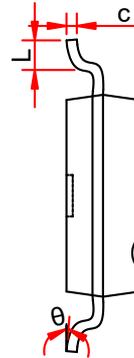
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250uA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V			1	uA
Gate-to-source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20V			±100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250uA	1.3	1.8	2.5	V
Drain-to-source On-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 14A		6.5	8.5	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A		9.0	12.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 11A		17	25	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, F = 1.0MHz, V <sub>DS</sub> = 15 V		1250		Pf
Output Capacitance	C <sub>OSS</sub>			180		
Reverse Transfer Capacitance	C <sub>RSS</sub>			144		
Gate resistance	R <sub>g</sub>	F=1MHz		1.8		Ω
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 11 A		26.5		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			2.1		
Gate-to-Source Charge	Q <sub>GS</sub>			4.3		
Gate-to-Drain Charge	Q <sub>GD</sub>			4.83		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 11A, R <sub>G</sub> = 6Ω		6.4		ns
Rise Time	t <sub>r</sub>			17.6		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			32.4		
Fall Time	t <sub>f</sub>			14		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1A		0.7	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 11A, di/dt = 100A/us		10.0		ns
Reverse Recovery Charge	Q <sub>rr</sub>				3.1	

**Typical Characteristics (Ta=25°C, unless otherwise noted)**

**Output Characteristics <sup>d</sup>**

**Transfer Characteristics <sup>d</sup>**

**On-Resistance vs. Drain Current <sup>d</sup>**

**On-Resistance vs. Gate to Source Voltage <sup>d</sup>**

**On-Resistance vs. Junction Temperature <sup>d</sup>**

**Threshold Voltage vs. Temperature**

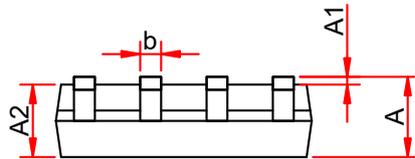

**Capacitance**

**Body Diode Forward Voltage<sup>d</sup>**

**Single Pulse power**

**Safe Operating Power**

**Gate Charge Characteristics**



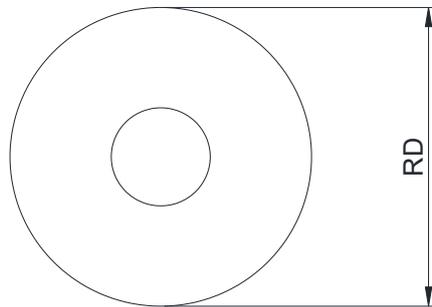
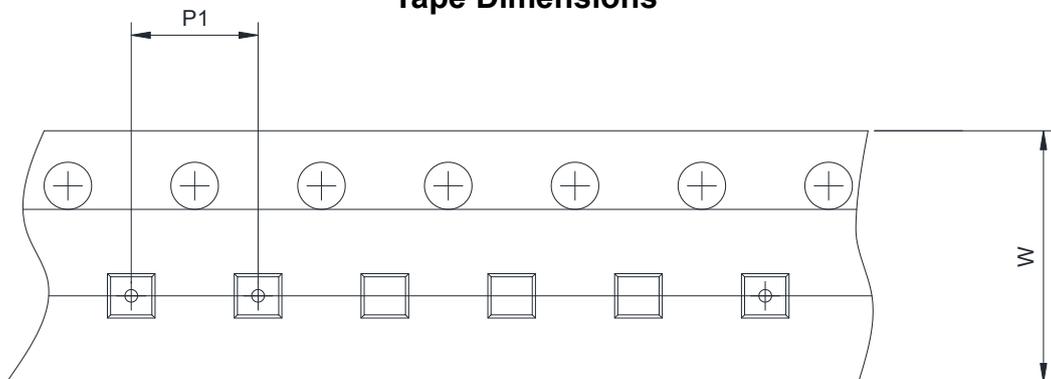
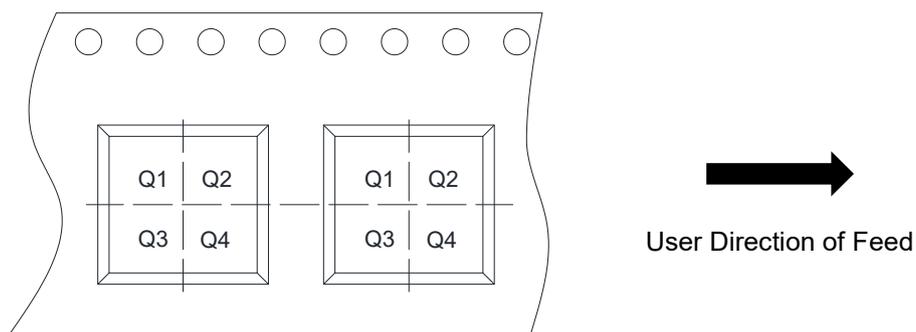
**Transient thermal response (Junction-to-Ambient)**

**PACKAGE OUTLINE DIMENSIONS**
**SOP-8L**

**TOP VIEW**

**SIDE VIEW**

I) NA

 II) 

**SIDE VIEW**

Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	1.35	1.55	1.75
A1	0.05	0.15	0.25
A2	1.25	1.40	1.65
b	0.33	-	0.51
c	0.15	-	0.26
D	4.70	4.90	5.10
E	3.70	3.90	4.10
E1	5.80	6.00	6.20
e	1.27BSC		
L	0.40	-	1.27
$\theta$	0°	-	8°

**TAPE AND REEL INFORMATION**
**Reel Dimensions**

**Tape Dimensions**

**Quadrant Assignments For PIN1 Orientation In Tape**


RD	Reel Dimension	<input type="checkbox"/> 7inch	<input checked="" type="checkbox"/> 13inch		
W	Overall width of the carrier tape	<input type="checkbox"/> 8mm	<input checked="" type="checkbox"/> 12mm		
P1	Pitch between successive cavity centers	<input type="checkbox"/> 2mm	<input type="checkbox"/> 4mm	<input checked="" type="checkbox"/> 8mm	
Pin1	Pin1 Quadrant	<input checked="" type="checkbox"/> Q1	<input type="checkbox"/> Q2	<input type="checkbox"/> Q3	<input type="checkbox"/> Q4